

Secondary Side Post Regulator for AC/DC and DC/DC Multiple Output Converters

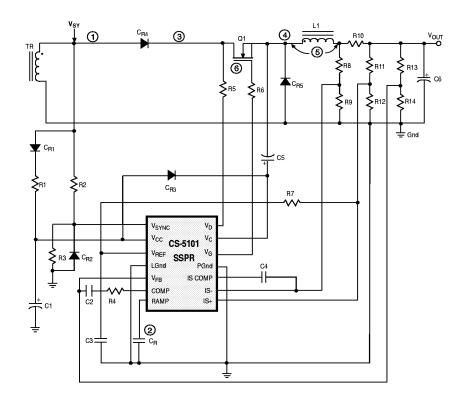
Description

The CS-5101 is a bipolar monolithic secondary side post regulator (SSPR) which provides tight regulation of multiple output voltages in AC-DC or DC-DC converters. Leading edge pulse width modulation is used with the CS-5101.

The CS-5101 is designed to operate over an 8V to 45V supply voltage (V_{CC}) range and up to a 75V drive voltage (V_{C}).

The CS-5101 features include a totem pole output with 1.5A peak output current capability, externally programmable overcurrent protection, an on chip 2% precision 5V reference, internally compensated error amplifier, externally synchronized switching frequency, and a power switch drain voltage monitor. It is available in a 14 lead plastic DIP or a 16 lead wide body SO package.

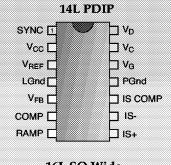
Application Diagram

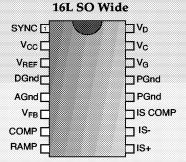


Features

- 1.5A Peak Output (Grounded Totem Pole)
- 8V to 75V Gate Drive Voltage
- 8V to 45V Supply Voltage
- 300ns Propagation Delay
- 1% Error Amplifier Reference Voltage
- Lossless Turn On and Turn Off
- Sleep Mode: < 100μA
- Overcurrent Protection with Dedicated Differential Amp
- Synchronization to External Clock
- External Power Switch Drain Voltage Monitor

Package Options







Cherry Semiconductor Corporation 2000 South County Trail East Greenwich, Rhode Island 02818-1530 Tel: (401)885-3600 Fax (401)885-5786 email: info@cherry-semi.com

A CHERRY Company

Absolute Maximum Ratings	
Power Supply Voltage, V _{CC}	0.3V to 45V
V _{SYNC} and Output Supply Voltages, V _C , V _G , V _{SYNC} , V _D	
V _{IS} +, V _{IS} - (V _{CC} – 4V, up to 24V)	0.3 to 24V
V _{REF} , V _{FB} , V _{COMP} , V _{RAMP} , V _{ISCOMP}	0.3 to 10V
Operating Junction Temperature, T _J	-40 to 150°C
Operating Temperature Range	40 to 85°C
Storage Temperature Range	65 to 150°C
Output Energy (capacitive load per cycle)	5μJ
ESD Human Body	2kV
ESD Machine Model	200V
Lead Temperature Soldering	
Wave Solder (through hole styles only)	10 sec. max, 260°C peak
Reflow (SMD styles only)	60 sec. max above 183°C 230°C neak

Wave Solder (through hole styles only) Reflow (SMD styles only)						
Electrical Characteristics: -40°C ≤	$T_A \le 85^{\circ}C; -40^{\circ}C \le T_J \le 150^{\circ}C; 10V < V_{CC} < 40^{\circ}C$	5V; 8V < V	⊂<75V unless	otherwise sp	ecified.	
PARAMETER	TEST CONDITIONS	MIN		MASS	UNIT	
Error Amplifier						
Input Voltage Initial Accuracy	$V_{FB} = V_{COMP}; V_{CC} = 15V;$ T = 25°C (Note 1)	1.98	2.00	2.02	V	
Input Voltage	$V_{FB} = V_{COMP}$, includes line and temp	1.94	2.00	2.06	V	
Input Bias Current	$V_{FB} = 0V$; IV_{FB} flows out of pin			500	nΑ	
Open Loop Gain	$1.5V < V_{COMP} < 3.0V$	60	70		dB	
Unity Gain Bandwidth	$1.5V < V_{COMP} < 3.0V$; (Note 1)	0.7	1.0		MH	
Output Sink Current	$V_{COMP} = 2.0V; V_{FB} = 2.2V$	2	8		mA	
Output Source Current	$V_{COMP} = 2.0V; V_{FB} = 1.8V$	2	6		mA	
V _{COMP} High	$V_{FB} = 1.8V$	3.3	3.5	3.7	V	
V _{COMP} Low	$V_{FB} = 2.2V$	0.85	1.0	1.15	V	
PSRR	$10V < V_{CC} < 45V;$ $V_{FB} = V_{COMP} \text{ (Note 1)}$	60	70		dB	
Voltage Reference Output Voltage Initial Accuracy	$V_{CC} = 15V; T = 25^{\circ}C \text{ (Note 1)}$	4.9	5.0	5.1	V	
		4.8	5.0	5.2	V	
Output Voltage Line Regulation	$0A < I_{REF} < 8mA$	4.0	10	60	mV	
-	$10V < V_{CC} < 45V; I_{REF} = 0A$		20	60		
Load Regulation Current Limit	$0A < I_{REF} < 8mA$	10	50	00	mV mA	
V _{REF} OK FAULT V	$V_{REF} = 4.8V$ $V_{SYNC} = 5V$; $V_{REF} = V_{LOAD}$	4.10	4.40	4.60	V	
V _{REF} OK V		4.30	4.50	4.80	V	
V _{REF} OK V V _{REF} OK Hysteresis	$V_{SYNC} = 5V; V_{REF} = V_{LOAD}$	40	100	250	mV	
Current Sense Amplifier						
IS COMP High V	$IS^+ = 5V$; $IS^- = IS COMP$	4.7	5.0	5.3	V	
IS COMP Low V	$IS^+ = 0V$; $IS^- = IS COMP$	0.5	1.0	1.3	V	
Source Current	$IS^{+} = 5V; IS^{-} = 0V$	2.0	10		mA	
Sink Current	$IS^{-} = 5V; IS^{+} = 0V$	10	20		mA	
Open Loop Gain	$1.5V \le V_{COMP} \le 4.5V$; $R_L = 4k\Omega$	60	80		dB	
CMRR	(Note 1)	60	80		dB	
PSRR	10V < V _{CC} < 45V, (Note 1)	60	80		dB	
	- -					

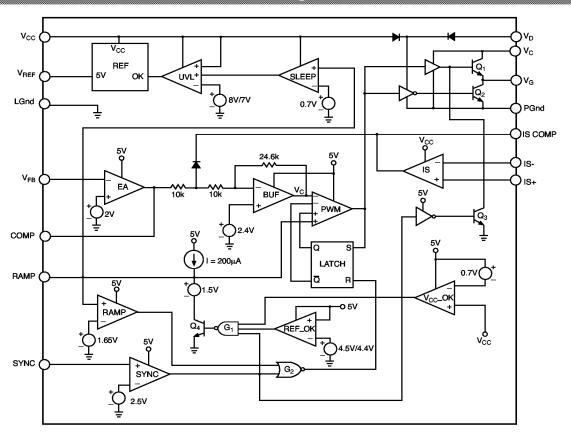
PARAMETER	TEST CONDITIONS	MIN	TYP		UNIT
Current Sense Amplifier: contin	ued				
Input Offset Voltage	V_{IS} + = 2.5V; V_{IS} - = V_{ISCOMP}	-8	0	8	mV
Input Bias Currents	$V_{IS}^+ = V_{IS}^- = 0V$; I_{IS} flows out of pins		20	250	nΑ
Input Offset Current (IS+, IS-)		-250	0	250	nΑ
Input Signal Voltage Range	(Note 1)	-0.3		V _{CC} -4.0	V
RAMP/SYNC Generator					
Ramp Source Current Initial Accuracy	$V_{SYNC} = 5V, V_{RAMP} = 2.5V ; T = 25^{\circ}C$ (Note 1)	0.18	0.20	0.22	mA
Ramp Source Current	$V_{SYNC} = 5V$; $V_{RAMP} = 2.5V$	0.16	0.20	0.24	mA
Ramp Sink Current	$V_{SYNC} = 0V; V_{RAMP} = 2.5V$	1.0	4.0		mA
RAMP Peak Voltage	$V_{SYNC} = 5V$	3.3	3.5	3.7	V
RAMP Valley Voltage	$V_{SYNC} = 0V$	1.4	1.5	1.6	V
RAMP Dynamic Range	$V_{RAMPDR} = V_{RAMPPK} - V_{RAMPVY}$	1.7	2.0	2.3	V
RAMP Sleep Threshold Voltage	$V_{RAMP} @ V_{REF} < 2.0V$	0.3	0.6	1.0	V
SYNC Threshold	$V_{SYNC} @ V_{RAMP} > 2.5V$	2.3	2.5	2.7	V
SYNC Input Bias Current	$V_{SYNC} = 0V$; I_{SYNC} flows out of pin		1	20	μΑ
Output Stage					
V _G , High	$V_{SYNC} = 5V; IV_G = 200mA, V_C - V_G$		1.6	2.5	V
V _G , Low	$V_{SYNC} = 0V$; $IV_G = 200mA$		0.9	1.5	V
V_G Rise Time	Switch V_{SYNC} High; $C_G = 1nF$;		30	7 5	ns
	V_{CC} = 15V; measure 2V to 8V				
V _G Fall Time	Switch V_{SYNC} Low; $C_G = 1nF$ $V_{CC} = 15V$; measure 8V to 2V		40	100	ns
V _G Resistance to Gnd	Remove supplies; $V_G = 10V$		50	100	kΩ
V _D Resistance to Gnd	Remove supplies; V _D = 10V	500	1500		Ω
General					
I _{CC} , Operating	$V_{SYNC} = 5V$		12	18	mΑ
I _{CC} in UVL	$V_{CC} = 6V$		300	500	μΑ
I _{CC} in Sleep Mode High	$V_{RAMP} = 0V; V_{CC} = 45V$		80	200	μΑ
I _{CC} In Sleep Mode Low	$V_{RAMP} = 0V; V_{CC} = 10V$		20	50	μΑ
I _C , Operating High	$V_{SYNC} = 5V; V_{FB} = V_{IS} - = 0V;$ $V_{C} = 75V$		4	8	mA
I _C Operating Low	$V_{SYNC} = 5V; V_{FB} = V_{IS} = 0V; V_C = 8V$		3	6	mA
UVLO Start Voltage		7.4	8.0	9.2	V
UVLO Stop Voltage		6.4	7.0	8.3	V
UVLO Hysteresis		0.8	1.0	1.2	V
Leading Edge, t _{DELAY}	$V_{SYNC} = 2.5V$ to $V_G = 8V$		280		ns
Trailing Edge, t _{DELAY}	$V_{SYNC} = 2.5V$ to $V_G = 2V$		<i>7</i> 50		ns

Note 1: Guaranteed by design. Not 100% tested in production.

5101		Packa	ge Pin Description	
	- I		FUNCTION	
14L PDIP	16L SO Wide			
1	1	SYNC	Synchronization input.	
2	2	v_{cc}	Logic supply (10V to 45V).	
3	3	$ m V_{REF}$	5.0V voltage reference.	
4		LGnd	Logic level ground (Analog and digital ground tied).	
5	6	$ m V_{FB}$	Error amplifier inverting input.	
6	7	COMP	Error amplifier output and compensation.	
7	8	RAMP	RAMP programmable with the external capacitor.	
8	9	IS+	Current sense amplifier non-inverting input.	
9	10	IS-	Current sense amplifier inverting input.	
10	11	IS COMP	Current sense amplifier compensation and output.	
11	12, 13	PGnd	Power ground.	
12	14	V_G	External power switch gate drive.	
13	15	V_{C}	Output power stage supply voltage (8V to 75V).	
14	16	V_{D}	External FET DRAIN Voltage Monitor.	
	5	AGnd	Analog Ground.	
	4	DGnd	Digital Ground.	

Circuit Description

Block Diagram



Circuit Description: continued

Theory of Operation

The CS-5101 is designed to regulate voltages in multiple output power supplies. Functionally, it is similar to a magnetic amplifier, operating as a switch with a delayed turn-on. It can be used with both single ended and dual ended topologies.

The V_{FB} voltage is monitored by the error amplifier EA. It is compared to an internal reference voltage and the amplified differential signal is fed through an inverting amplifier into the buffer, BUF. The buffered signal is compared at the PWM comparator with the ramp voltage generated by capacitor C_R . When the ramp voltage V_R , exceeds the control voltage V_C , the output of the PWM comparator goes high, latching its state through the LATCH, the output stage transistor Q_1 turns on, and the external power switch, usually an N-FET, turns on.

SYNC Function

The SYNC circuit is activated at time t_1 (Figure 1) when the voltage at the SYNC pin exceeds the threshold level (2.5V) of the SYNC comparator. The external ramp capacitor C_R is allowed to charge through the internal current source I (200 μ A). At time t_2 , the ramp voltage intersects with the control voltage V_C and the output of the PWM comparator goes high, turning on the output stage and the external power switch. At the same time, the PWM comparator is latched by the RS latch, LATCH.

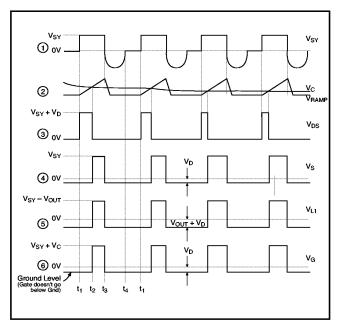


Figure 1. Waveforms for CS-5101. The number to the left of each curve refers to a node on the Application Diagram.

The logic state of the LATCH can be changed only when both the voltage level of the trailing edge of the power pulse at the SYNC pin is less than the threshold voltage of the SYNC comparator (2.5V) and the RAMP voltage is less than the threshold voltage of the RAMP comparator (1.65V). On the negative going transition of the secondary side pulse V_{SY} , gate G_2 output goes high, resetting the latch at time t_3 . Capacitor C_R is discharged through transistor Q_4 . C_R 's output goes low disabling the output stage, and the external power switch (an N-FET) is turned off.

RAMP Function

The value of the ramp capacitor C_R is based on the switching frequency of the regulator and the maximum duty cycle of the secondary pulse V_{SY} . If the RAMP pin is pulled externally to 0.3V or below, the SSPR is disabled. Current drawn by the IC is reduced to less than $100\mu A$, and the IC is in SLEEP mode.

FAULT Function

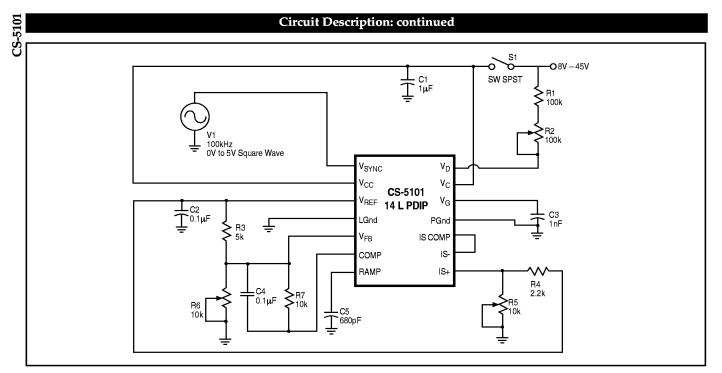
The voltage at the V_{CC} pin is monitored by the undervoltage lockout comparator with hysteresis. When V_{CC} falls below the UVL threshold, the 5V reference and all the circuitry running off of it is disabled. Under this condition the supply current is reduced to less than $500\mu A$.

The V_{CC} supply voltage is further monitored by the V_{CC} -OK comparator. When V_{CC} is reduced below V_{REF} - 0.7V, a fault signal is sent to gate G_1 . This fault signal, which determines if V_{CC} is absent, works in conjunction with the ramp signal to disable the output, but only after the current cycle has finished and the RS latch is reset. Therefore this fault will not cause the output to turn off during the middle of an on pulse, but rather will utilize lossless turn-off. This feature protects the FET from overvoltage stress. This is accomplished through gate G_1 by driving transistor Q_4 on.

An additional fault signal is derived from the REF_OK comparator. V_{REF} is monitored so to disable the output through gate G_1 when the V_{REF} voltage falls below the OK threshold. As in the V_{CC} OK fault, the REF_OK fault disables the output after the current cycle has been completed. The fault logic will operate normally only when V_{REF} voltage is within the specification limits of REF_OK.

DRAIN Function

The drain pin, V_D monitors the voltage on the drain of the power switch and derives energy from it to keep the output stage in an off state when V_C or V_{CC} is below the minimum specified voltage.



CS-5101 bench test

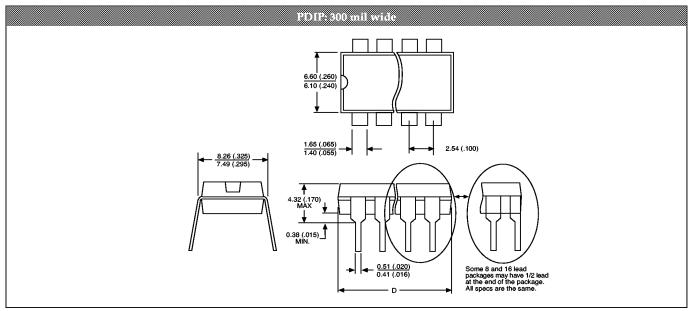
Package Specification

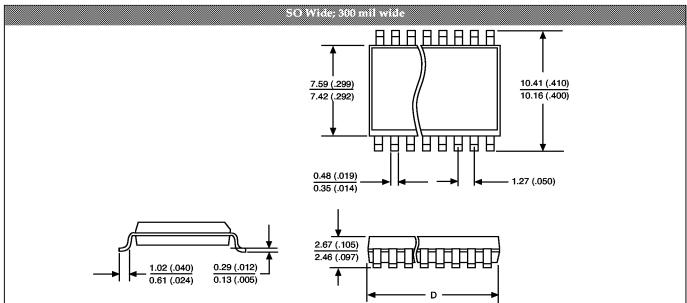
PACKACH DIMPNISTONS IN MEDITACHES

	D			
Lead Count	Me	tric	Eng	glish
	Max	Min	Max	Min
14L PDIP	19.18	18.92	.755	.745
16L SO Wide	10.46	10.21	.412	.402

PACKAGO TERMALDATA

Thermal Data		16L SOIC	14L PDIP	
$R_{\Theta JC}$	typ	23	48	°C/W
$R_{\Theta JA}$	typ	105	85	°C/W





Contenting to the second

Part Number	Description
CS-5101N14	14L PDIP
CS-5101DW16	16L SO Wide
CS-5101DWR16	16L SO Wide Tape & Reel

Cherry Semiconductor Corporation reserves the right to make changes to the specifications without notice. Please contact Cherry Semiconductor Corporation for the latest available information.

PATENTS PENDING